

Experiment - 6Title of the experiment:

Determination of energy bandgap of a Semiconductor by four probe method

Objective:

To determine the bandgap of a semiconductor by measuring the resistivity as a function of temperature using four probe method

Equipment list:

1. Spring loaded four probes
2. Germanium (semiconductor) Crystal
3. Oven (up to  $150^{\circ}\text{C}$ )
4. Thermometer
5. Constant Current Source (a)
6. voltmeter

Formula:

$E_g$  = Energy difference between valence band and Conduction band

$$\rho(T) = \rho_0 \exp\left(\frac{E_g}{2KT}\right)$$

$\rho$  = resistivity

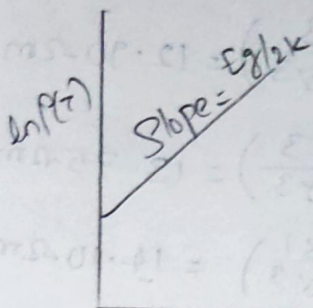
$\rho_0$  = Residual resistivity

$T$  = temperature

$$\rho(T) = \rho_0 \exp\left(\frac{E_g}{2KT}\right)$$

$$\ln \rho(T) = \ln \rho_0 + \ln \exp\left(\frac{E_g}{2KT}\right)$$

$$\ln \rho(T) = \ln \rho_0 + \frac{E_g}{2KT}$$



$$P = CF \left( \frac{V}{I} \right)$$

CF = Correction factor

$$P = 0.213 \text{ cm} \left( \frac{V}{I} \right)$$

$I$  = Current passing through semiconductor

$V$  = measured voltage

$$CF = 0.213 \text{ cm}$$

Laboratory report :-

$$\text{Current } I = 5 \times 10^{-3} \text{ A}$$

| S/No | Temperature (K) | voltage (V) | Resistivity $P = CF(V/I)$ | $1/T$ ( $K^{-1}$ ) | $\log P$ |
|------|-----------------|-------------|---------------------------|--------------------|----------|
| 1    | 300K            | 0.303V      | 12.90 $\Omega \text{ m}$  | 0.0033 $K^{-1}$    | 2.55     |
| 2    | 313K            | 0.323V      | 13.75 $\Omega \text{ m}$  | 0.0031 $K^{-1}$    | 2.62     |
| 3    | 323K            | 0.331V      | 14.10 $\Omega \text{ m}$  | 0.0030 $K^{-1}$    | 2.64     |
| 4    | 333K            | 0.322V      | 13.71 $\Omega \text{ m}$  | 0.0030 $K^{-1}$    | 2.61     |
| 5    | 343K            | 0.315V      | 13.41 $\Omega \text{ m}$  | 0.0029 $K^{-1}$    | 2.59     |
| 6    | 353K            | 0.300V      | 12.78 $\Omega \text{ m}$  | 0.0028 $K^{-1}$    | 2.54     |
| 7    | 363K            | 0.223V      | 9.49 $\Omega \text{ m}$   | 0.0027 $K^{-1}$    | 2.25     |

Calculation :-

$$P = CF \left( \frac{V}{I} \right)$$



$$P_1 = 0.213 \times \left( \frac{0.303}{5 \times 10^{-3}} \right) = 12.90 \Omega m$$

$$P_2 = 0.213 \times \left( \frac{0.323}{5 \times 10^{-3}} \right) = 13.75 \Omega m$$

$$P_3 = 0.213 \times \left( \frac{0.331}{5 \times 10^{-3}} \right) = 14.10 \Omega m$$

$$P_4 = 0.213 \times \left( \frac{0.322}{5 \times 10^{-3}} \right) = 13.71 \Omega m$$

$$P_5 = 0.213 \times \left( \frac{0.315}{5 \times 10^{-3}} \right) = 13.41 \Omega m$$

$$P_6 = 0.213 \times \left( \frac{0.300}{5 \times 10^{-3}} \right) = 12.78 \Omega m$$

$$P_7 = 0.213 \times \left( \frac{0.223}{5 \times 10^{-3}} \right) = 9.49 \Omega m$$

$$\text{Slope } m = \frac{2.54 \cdot 2.25}{(2.83 - 2.75) \times 10^{-3}} = \frac{0.29}{0.08 \times 10^{-3}} = 3.625 \times 10^3$$

$$E_g = 2 \times k \times m$$

$$E_g = 2 \times 0.8617 \times 10^{-6} \times 3.625 \times 10^3$$

$$E_g = 0.62 \text{ eV}$$

Result:-

The band gap of intrinsic semiconductor of Germanium Crystal is  $= 0.62 \text{ eV}$

$$P = C \left( \frac{V}{T} \right)$$



